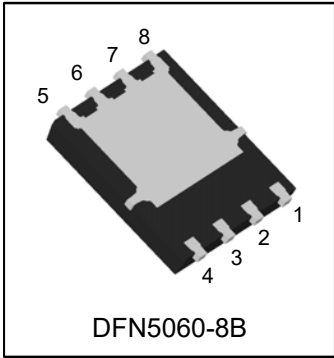


N7616D

N-Channel Enhancement Mode MOSFET



1. FEATURES

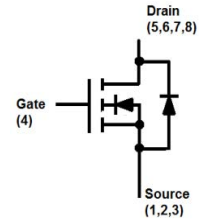
- Advanced trench cell design
- Low Thermal Resistance
- We declare that the material of product compliance with RoHS requirements and Halogen Free.

2. APPLICATIONS

- Motor drivers
- DC-DC Converter

3. DEVICE MARKING AND RESISTOR VALUES

Device	Marking	Shipping
N7616D	LN7616	3000/Tape&Reel



4. MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit
Drain-to-Source Voltage	VDS	100	V
Gate-to-Source Voltage	VGS	±20	V
Continuous Drain Current(TC = 25 °C, VGS = 10 V)	ID	59	A
Pulsed Drain Current(TC = 25 °C, VGS = 10 V)	IDM	236	A
Single Pulse Avalanche Energy L=0.1mH	EAS	13	mJ
Power Dissipation(TC = 25 °C)	PD	35	W
Operating Junction and Storage Temperature Range	Tj/Tstg	-55~+150	°C
Diode Forward Current	IS	55	A

5. THERMAL CHARACTERISTICS

Parameter	Symbol	Max	Unit
Thermal Resistance Junction-to-Ambient	RθJA	62.5	°C/W
Thermal Resistance Junction-to-Case	RθJC	3.5	

1. Surface Mounted on 1 in² pad area, t ≤ 10 sec



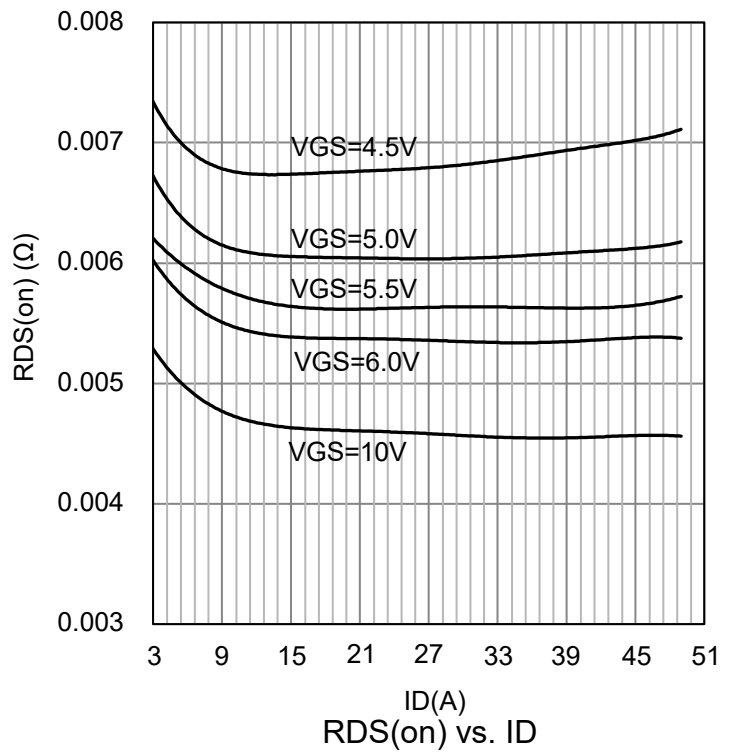
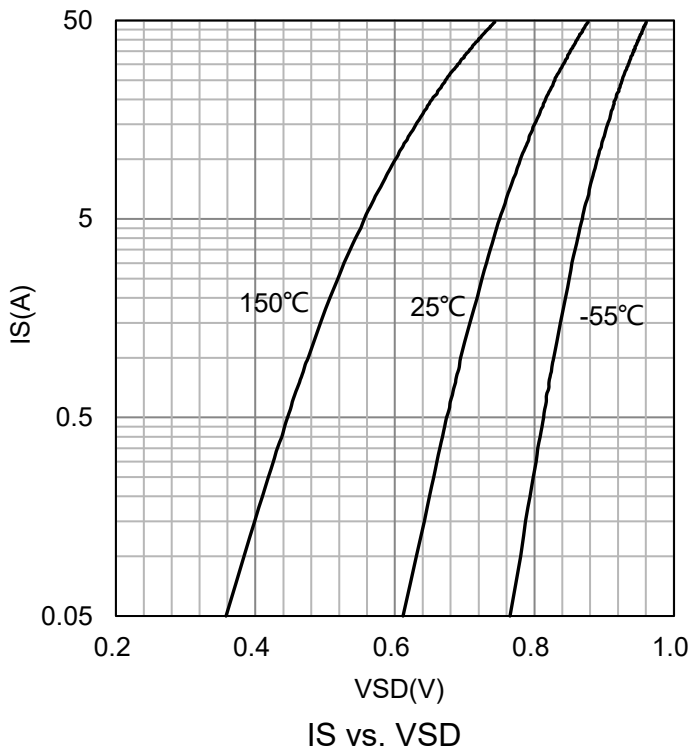
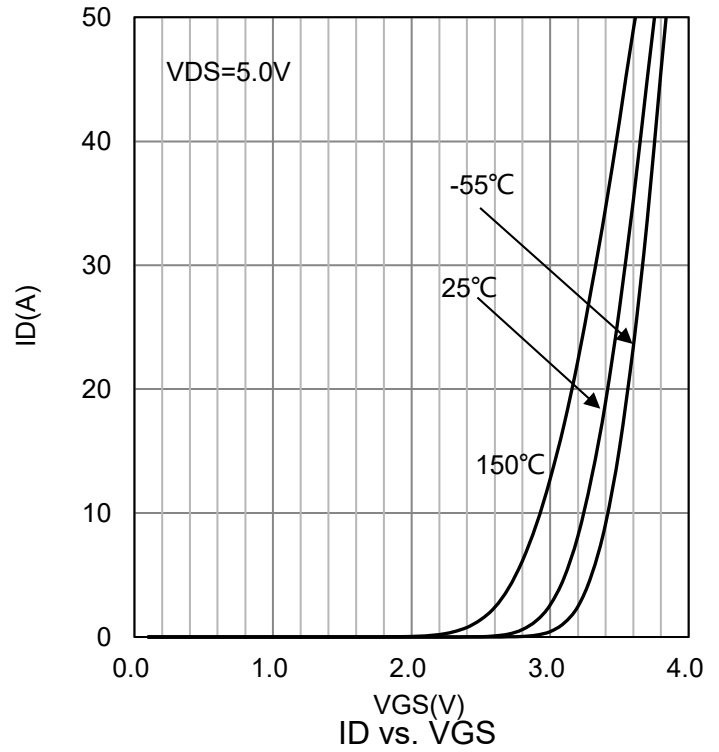
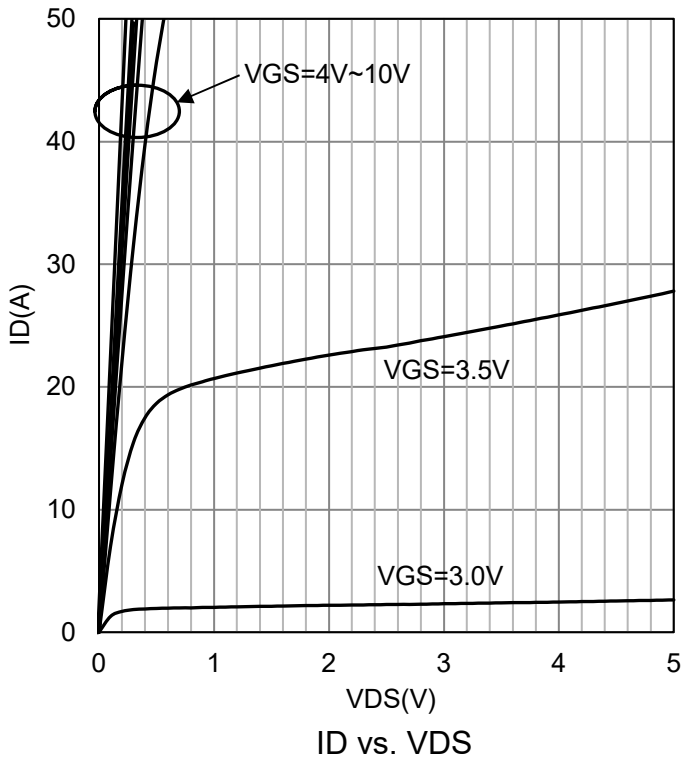
6. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Static					
Drain to Source Breakdown Voltage (VGS = 0V, ID = 250μA)	VDSS	100	-	-	V
Zero Gate Voltage Source Current (VDS = 80V, VGS = 0V) (VDS = 80V, VGS = 0V, TJ = 85 °C)	IDSS	-	-	1 30	uA
Gate-Body current (VDS = 0V, VGS = ±20V)	IGSS	-	-	±100	nA
Gate Threshold Voltage (VDS = VGS , ID = 250μA)	VGS(th)	1.5	-	2.5	V
Drain-to-Source On-Resistance (VGS = 10 V, ID = 20 A) (VGS = 6 V, ID = 10 A) (VGS = 4.5 V, ID = 10 A)	RDS(ON)	-	4.5 5.3 6	5.2 8 9	mΩ
Diode Forward Voltage (ISD = 20 A, VGS = 0 V)	VSD	-	0.8	1.2	V
Dynamic					
Input Capacitance	(VGS = 0V ,VDS = 50V, f = 1MHz)	Ciss	-	3353	-
Output Capacitance		Coss	-	520	-
Reverse Transfer Capacitance		Crss	-	5.2	-
Turn-on Delay Time	(VDS=50 V, VG EN=10V,RG = 6 Ω ID=13A)	td(on)	-	19	-
Rise Time		tr	-	4.7	-
Turn-Off Delay Time		td(off)	-	59.5	-
Fall Time		tf	-	21	-
Total Gate Charge (VDD=50V,VGS=10V,ID=13A)	Qg	-	55.7	72	nC
Total Gate Charge (VDD=50V,VGS=5V,ID=13A)	Qg	-	32	-	
Gate to Source Charge (VDD=40V,VGS=5V,ID=68A)	Qgs	-	11.8	-	
Gate to Drain Charge (VDD=40V,VGS=5V,ID=68A)	Qgd	-	14.4	-	
Gate Resistance (VDS=0V,VGS=0V,f=1.0MHz)	Rg	-	1	3	Ω
Reverse Recovery Time (VR=30V,IF=20 A, dI/dt = 100 A/us)	trr	-	65	-	ns
Reverse Recovery Charge (VR=30V,IF=20 A, dI/dt = 100 A/us)	Qrr	-	105	-	nC

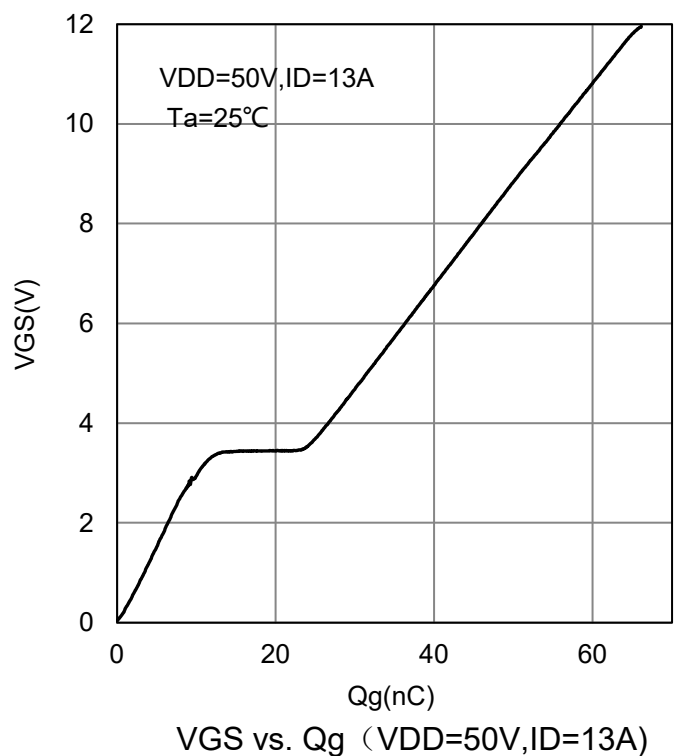
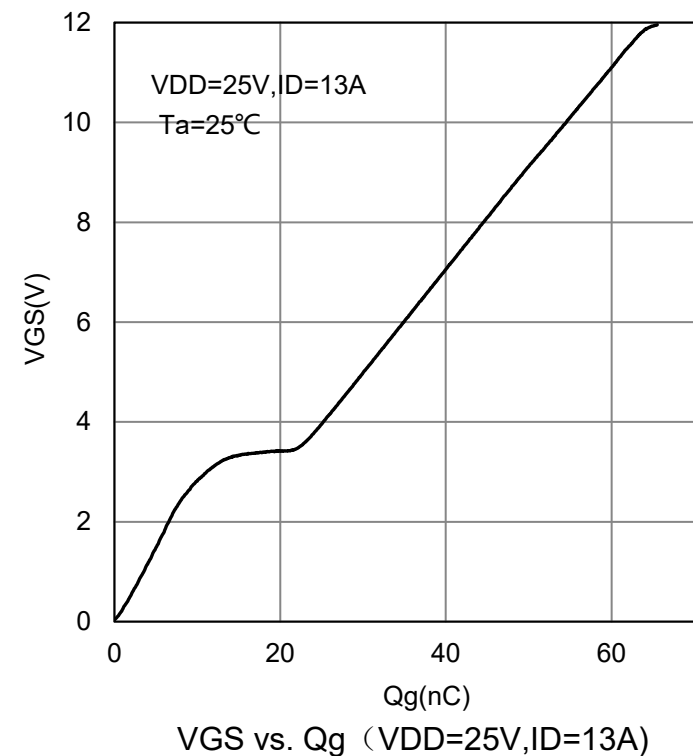
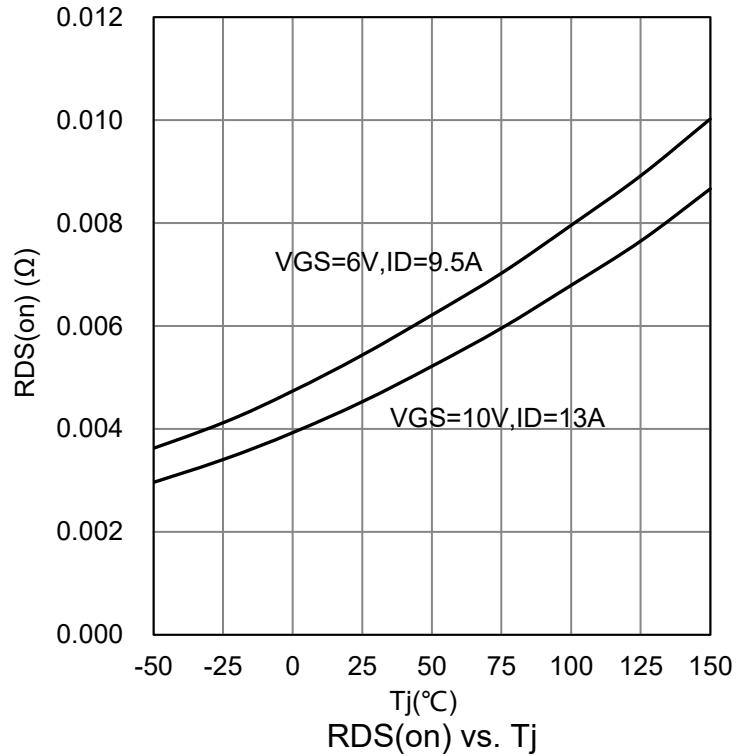
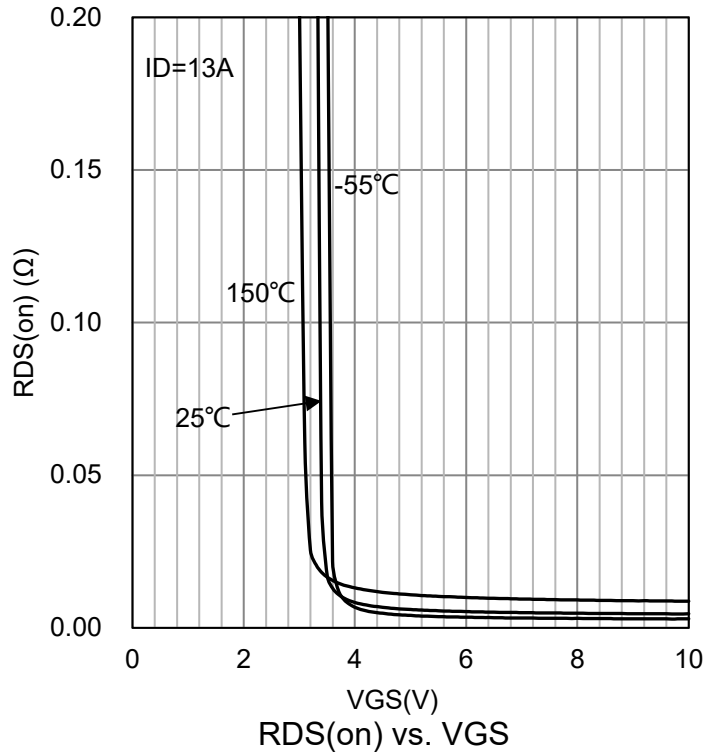
2.Pulse test ; pulse width ≤ 300μs, duty cycle ≤ 2 %



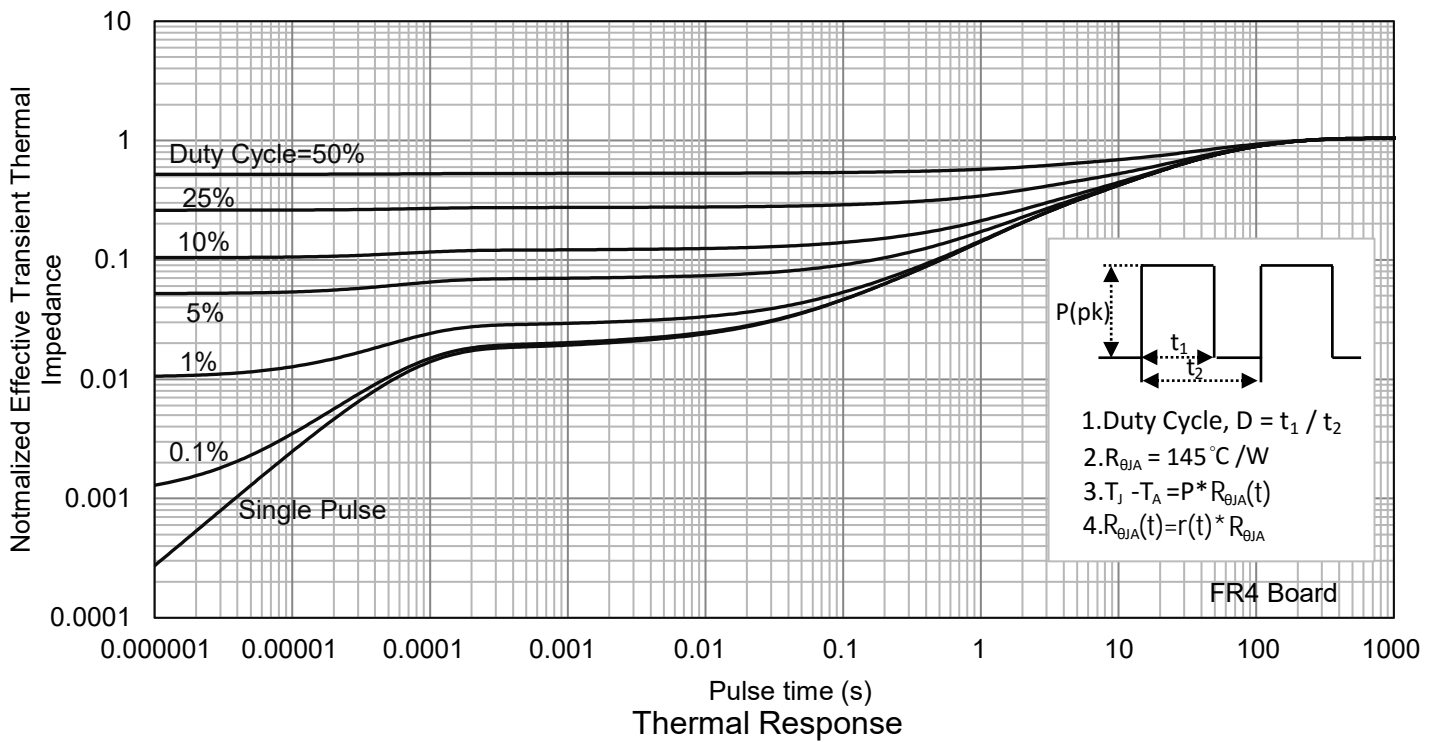
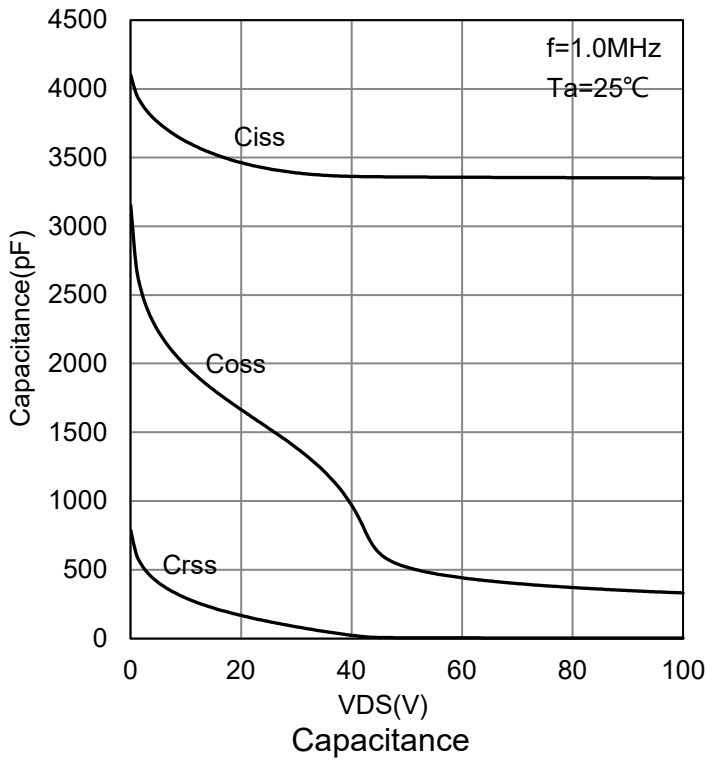
7.ELECTRICAL CHARACTERISTICS CURVES

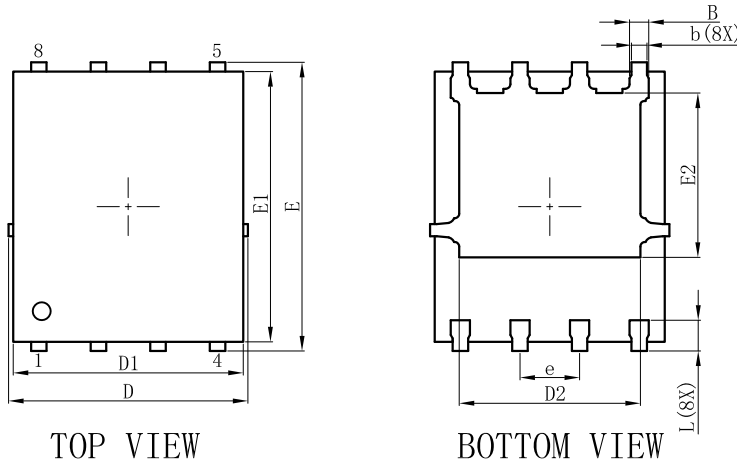


7.ELECTRICAL CHARACTERISTICS CURVES(Con.)



7.ELECTRICAL CHARACTERISTICS CURVES(Con.)

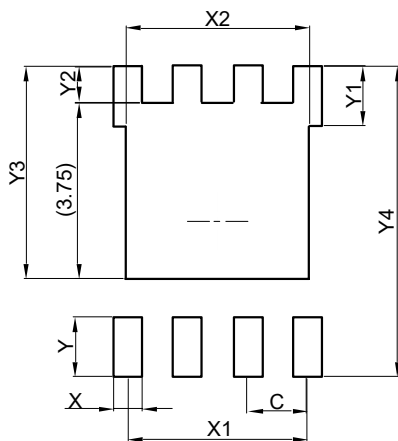


8. OUTLINE AND DIMENSIONS
DFN5060-8B


DFN5060-8B			
DIM	MIN	NOR	MAX
A	0.90	1.00	1.10
A1	0.00	0.02	0.05
E	6.00	6.15	6.30
E1	5.66	5.76	5.86
E2	3.40	3.50	3.60
D	4.95	5.10	5.25
D1	4.80	4.90	5.00
D2	3.76	3.86	3.96
b	0.30	0.35	0.40
B	0.36	0.41	0.46
L	0.56	0.66	0.76
e	1.27BSC		
c	0.254REF.		
θ	0°	-	12°
All Dimensions in mm			

GENERAL NOTES

1. Top package surface finish Ra0.4±0.2um
2. Bottom package surface finish Ra0.7±0.2um
3. Side package surface finish Ra0.4±0.2um
4. Protrusion or Gate Burrs shall not exceed 0.05mm per side.
5. Offcenter Max0.038mm; Mismatch Max 0.038mm.

9. SOLDERING FOOTPRINT


DFN5060-8B	
DIM	(mm)
C	1.27
X	0.61
X1	3.81
X2	3.91
Y	1.27
Y1	1.27
Y2	0.77
Y3	4.52
Y4	6.61

